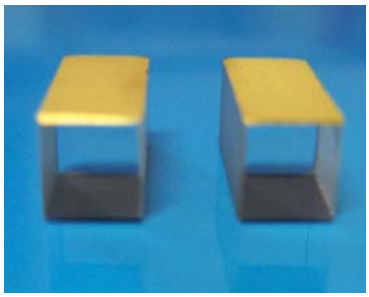
Laser Crystals
NLO Crystals
Birefringent Crystals
AO and EO Crystals

RTP Electro-optic Q-Switch

Introductions



Regular flux grown RTP has an electric resistivity as low as 10^8 Ω·cm, which may exhibit the detrimental electrochromism when subjected to a dc electric field. RTP crystals with high electrical resistivity (~10^{11}-10^{12}Ω·cm) have been grown successfully using our own proprietary technology. The electrochromism is not observed under a continuous 1000V/mm Z-directed electric field over more than 1000 hours. This RTP crystal has high damage threshold, large effective electro-optic coefficients and lower half-wave voltage. The Q-switch is built utilizing thermally compensated double-crystal designs.

Advantages:

High Damage Threshold
No Piezoelectric Ringing
Low Insertion Loss
Thermal Compensating Design
Non-hygroscopic
High Extinction and Contrast Ratio

Specification

Items	Specifications
Spectral range	350nm~4500nm
Half Wave Voltage at 1064 nm	5x5x10 mm: ~2,000 V 8x8x10 mm: ~3,200 V 9x9x20 mm: ~1,800 V
Contrast ratio	>100：1
Aperture	from 2x2 mm² up to 15x15 mm²
Damage threshold	> 750MW/cm^2 (@ 1064nm, 10ns, 10Hz)
AR coating	R < 0.2% @ 1064 nm

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Crystal | RTP 01